# P-Channel 60-V (D-S) MOSFET

### **Key Features:**

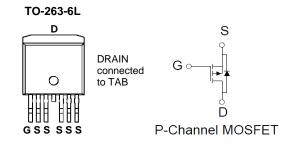
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

## **Typical Applications:**

- Load Switches
- DC/DC Conversion
- Motor Drives

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
-60	$7.5 @ V_{GS} = -10V$	-120 <sup>a</sup>	
-00	$9.5 @ V_{GS} = -4.5V$	-120	





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			-60	V		
Gate-Source Voltage			±20	V		
Continuous Drain Current a	T <sub>C</sub> =25°C	I <sub>D</sub>	-120			
Pulsed Drain Current <sup>b</sup>			-480	Α		
Continuous Source Current (Diode Conduction) a	T <sub>C</sub> =25°C	I <sub>S</sub>	-120	Α		
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	$P_{D}$	300	W		
Operating Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient °	$R_{\theta JA}$	62.5	°C/W		
Maximum Junction-to-Case	$R_{ heta JC}$	0.5	C/VV		

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#### Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

#### **Electrical Characteristics**

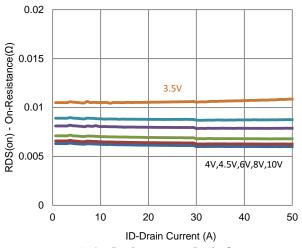
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-50			Α	
Dunin Course On Bonistones 8	r	$V_{GS} = -10 \text{ V}, I_D = -40 \text{ A}$			7.5	O	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -30 \text{ A}$			9.5	mΩ	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = -15 \text{ V}, I_{D} = -40 \text{ A}$		66		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -20 \text{ A}, V_{GS} = 0 \text{ V}$		-0.8		V	
	Dynamic <sup>b</sup>						
Total Gate Charge	$Q_g$	$V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V},$		109		nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -30 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -40 \text{ A}$		46			
Gate-Drain Charge	$Q_{gd}$	ID = -40 A		39			
Turn-On Delay Time	t <sub>d(on)</sub>	V 20 V D = 0.0 O		17			
Rise Time	t <sub>r</sub>	$V_{DS} = -30 \text{ V}, R_L = 0.8 \Omega,$ $I_D = -40 \text{ A},$		26		no	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		376		ns	
Fall Time	t <sub>f</sub>	V GEN = -10 V, 1\(\text{GEN} = 0.12\)		122			
Input Capacitance	C <sub>iss</sub>			7334			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		568		pF	
Reverse Transfer Capacitance	$C_{rss}$			378			

#### Notes

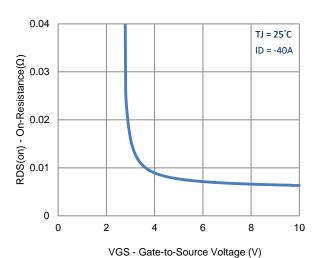
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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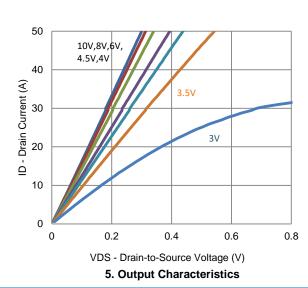
### **Typical Electrical Characteristics**

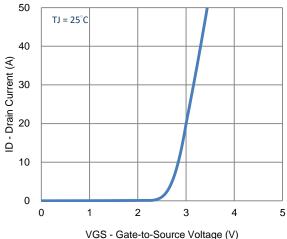


#### 1. On-Resistance vs. Drain Current

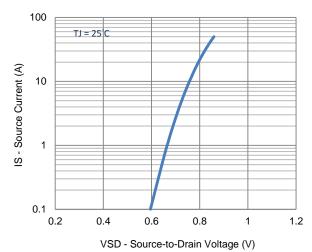


3. On-Resistance vs. Gate-to-Source Voltage

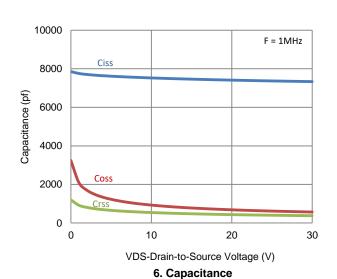




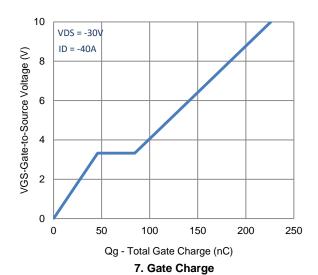
2. Transfer Characteristics

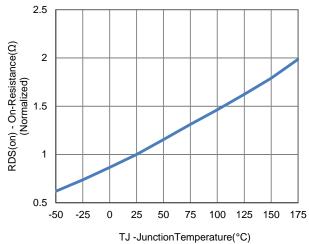


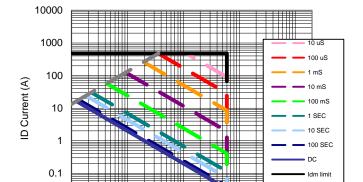
4. Drain-to-Source Forward Voltage



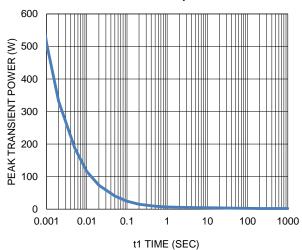
### **Typical Electrical Characteristics**







8. Normalized On-Resistance Vs Junction Temperature



VDS Drain to Source Voltage (V)

10

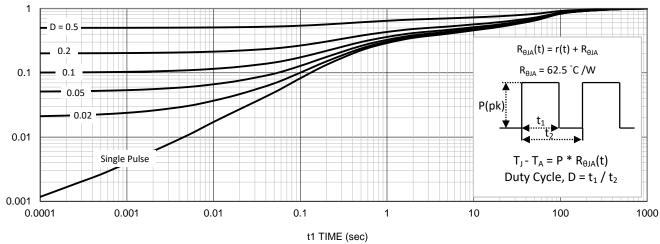
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9. Safe Operating Area

100

1000

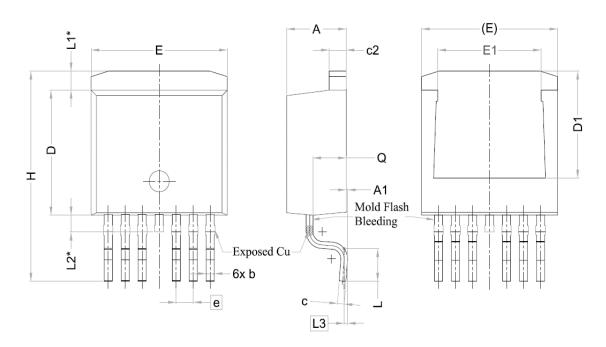
10. Single Pulse Maximum Power Dissipation

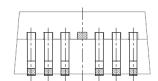


11. Normalized Thermal Transient Junction to Ambient

0.01 0.1

# **Package Information**





SYMBOL	DIMENSIONS			
STIVIBOL	MIN.	NOM.	MAX.	
Α	4.24	4.44	4.64	
A1	0.00	0.10	0.25	
b	0.50	0.60	0.70	
С	0.40	0.50	0.60	
c2	1.15	1,27	1.40	
D	8.82	8.92	9.02	
D1	6.86	7.65	_	
E	9.96	10.16	10.36	
E1	6.89	7.77	7.89	
е	1.27 BSC			
Н	14,61	15.00	15.88	
L	1.78	2.32	2.79	
L1	1.36 REF.			
L2	1,20 REF.			
L3	0.25 BSC			
Q	2.30	2.48	2.70	